# DATA SHEET



# Solid State Relay OCMOS FET

# **PS7221-2A**

# 8-PIN SOP 200 V BREAK DOWN VOLTAGE 2-ch Optical Coupled MOS FET

# DESCRIPTION

The PS7221-2A is solid state relay containing GaAs LEDs on the light emitting side (input side) and MOS FETs on the output side.

It is suitable for analog signal control because of their low offset and high linearity.

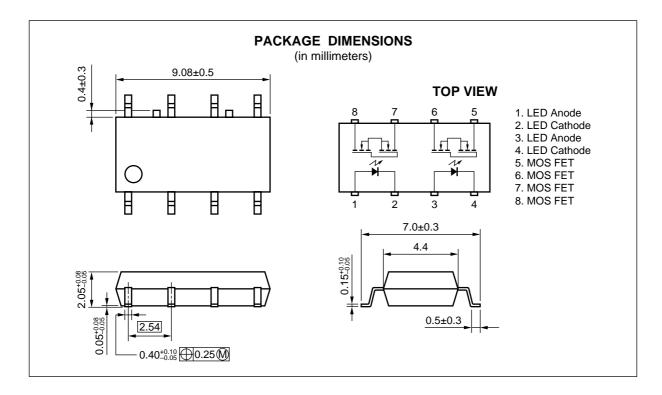
# **\*** FEATURES

- 2 channel type (1 a + 1 a output)
- Low LED operating current (IF = 2 mA)
- Designed for AC/DC switching line changer
- Small and thin package (8-pin SOP, Height = 2.1 mm)
- · Low offset voltage
- Ordering number of taping product: PS7221-2A-F3, F4
- UL approved: File No. E72422 (S)
- BSI approved: No. 8241/8242
- CSA approved: No. CA 101391

# APPLICATIONS

- Exchange equipment
- Measurement equipment
- FA/OA equipment

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# ★ ORDERING INFORMATION

Part Number	Package	Packing Style	Application Part Number <sup>*1</sup>
PS7221-2A	8-pin SOP	Magazine case 45 pcs	PS7221-2A
PS7221-2A -F3		Embossed Tape 1 500 pcs/reel	
PS7221-2A -F4			

\*1 For the application of the Safety Standard, following part number should be used.

# ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit	
Diode	Forward Current (DC)	lf	50	mA	
	Reverse Voltage	Vr	5.0	V	
	Power Dissipation	PD	50	mW/ch	
	Peak Forward Current <sup>1</sup>	IFP	1	А	
MOS FET	MOS FET Break Down Voltage		200	V	
	Continuous Load Current	IL.	150	mA	
	Pulse Load Current <sup>*2</sup> (AC/DC Connection)	Ilp	400	mA	
	Power Dissipation	PD	180	mW/ch	
Isolation Voltage <sup>*3</sup>		BV	1 500	Vr.m.s.	
Total Power Dissipation		Рт	460	mW	
Operating Ambient Temperature		TA	-40 to +80	°C	
Storage Temperature		Tstg	-40 to +100	°C	

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\*1 PW = 100  $\mu$ s, Duty Cycle = 1 %

\*2 PW = 100 ms, 1 shot

\*3 AC voltage for 1 minute at TA = 25 °C, RH = 60 % between input and output

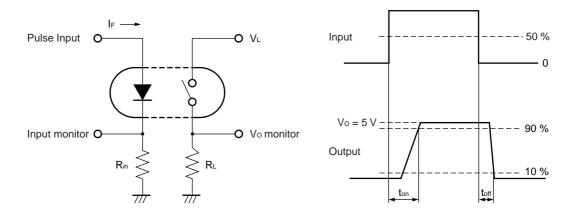
# **RECOMMENDED OPERATING CONDITIONS (TA = 25 °C)**

	Parameter	Symbol	MIN.	TYP.	MAX.	Unit
*	LED Operating Current	lF	2	10	20	mA
	LED Off Voltage	VF	0		0.5	V

# \* ELECTRICAL CHARACTERISTICS (TA = 25 °C)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	VF	IF = 10 mA		1.2	1.4	V
	Reverse Current	Ir	V <sub>R</sub> = 5 V			5.0	μA
MOS FET	Off-state Leakage Current	Loff	V <sub>D</sub> = 200 V		0.03	1.0	μA
	Output Capacitance	Cout	$V_{D} = 0 V, f = 1 MHz$		88		pF/ch
Coupled	LED On-state Current	IFon	l∟ = 150 mA			2.0	mA
	On-state Resistance	Ron1	IF = 10 mA, IL = 10 mA		4.0	8.0	Ω
		Ron2	$I_F$ = 10 mA, $I_L$ = 150 mA, $t \leq$ 10 ms				
	Turn-on Time <sup>™</sup>	ton	$I_{F}$ = 10 mA, Vo = 5 V, PW $\geq$ 10 ms		0.16	1.0	ms
	Turn-off Time <sup>™</sup>	toff			0.02	0.2	
	Isolation Resistance	Ri-o	VI-O = 1.0 kVDC	10 <sup>°</sup>			Ω
	Isolation Capacitance	CI-0	V = 0 V, f = 1 MHz		0.4		pF/ch

\*1 Test Circuit for Switching Time

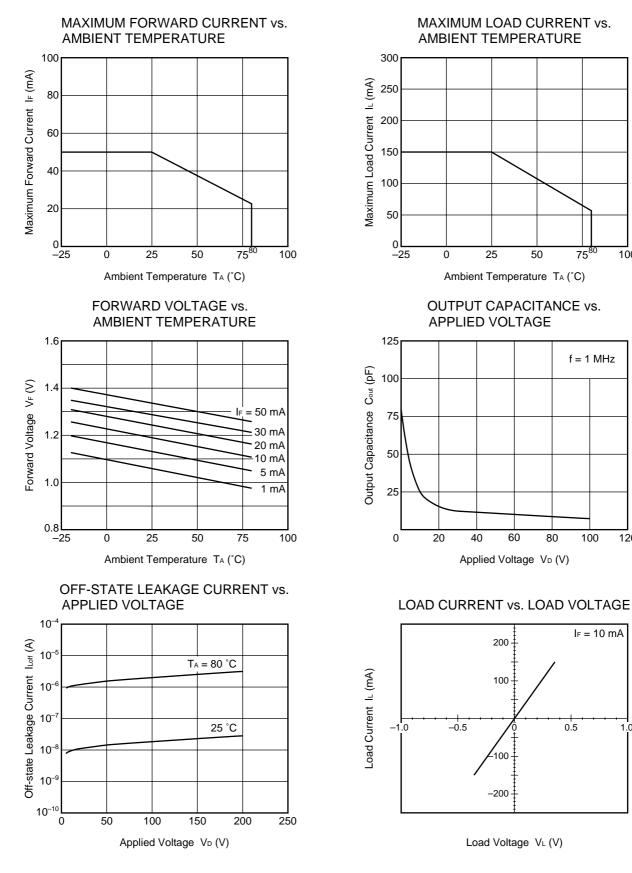


100

120

1.0

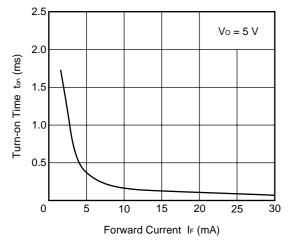
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise specified)



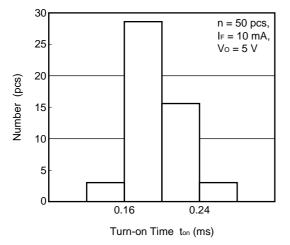
#### NORMALIZED ON-STATE RESISTANCE vs. AMBIENT TEMPERATURE 3.0 Normalized to 1.0 Normalized On-state Resistance Ron at T<sub>A</sub> = 25 °C, 2.5 I⊧ = 10 mA, I∟ = 10 mA 2.0 1.5 1.0 0.5 0.0 25 -25 0 50 75 100

Ambient Temperature  $T_A$  (°C)

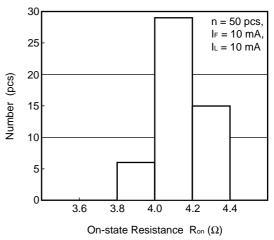
# TURN-ON TIME vs. FORWARD CURRENT



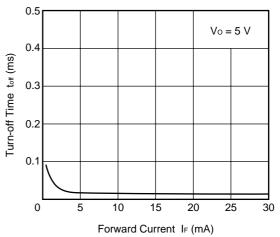
#### TURN-ON TIME DISTRIBUTION



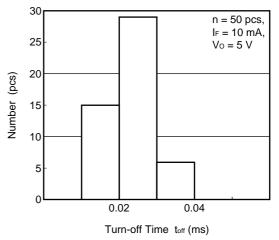
ON-STATE RESISTANCE DISTRIBUTION

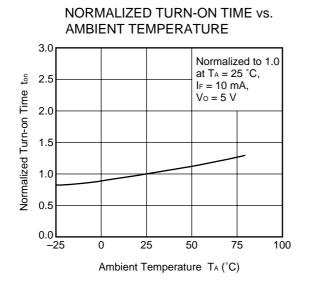


TURN-OFF TIME vs. FORWARD CURRENT

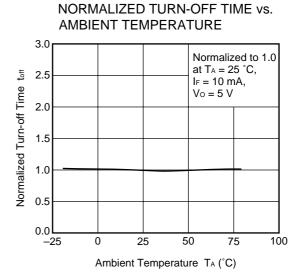


TURN-OFF TIME DISTRIBUTION

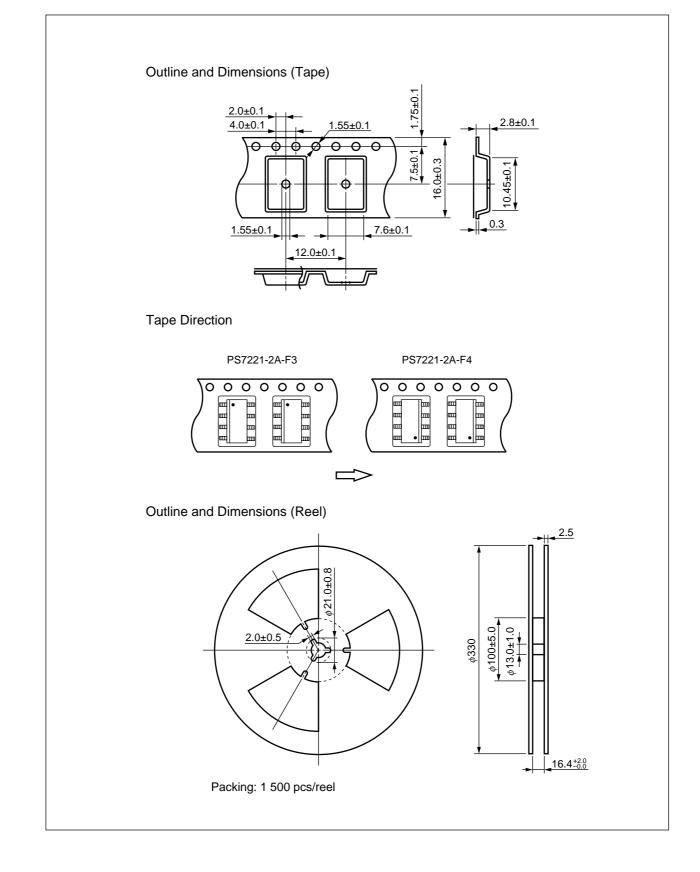




**Remark** The graphs indicate nominal characteristics.



# ★ TAPING SPECIFICATIONS (in millimeters)



# ★ RECOMMENDED SOLDERING CONDITIONS

# (1) Infrared reflow soldering

Peak reflow temperature
 235 °C (package surface temperature)

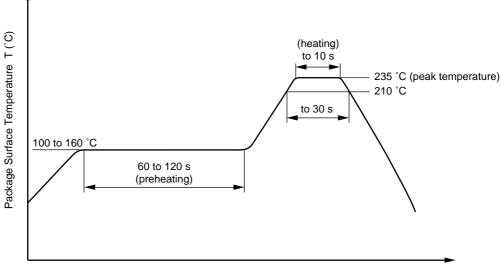
Two

- Time of temperature higher than 210 °C
- Number of reflows
- Flux

Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

## Recommended Temperature Profile of Infrared Reflow

30 seconds or less





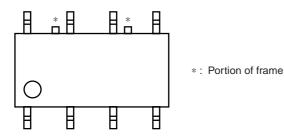
### (2) Dip soldering

- Temperature 260 °C or below (molten solder temperature)
- Time
- 10 seconds or less
- Number of times One
- Flux

Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

# (3) Cautions

- Fluxes
  - Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.
- Avoid shorting between portion of frame and leads.



[MEMO]

[MEMO]

# CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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